

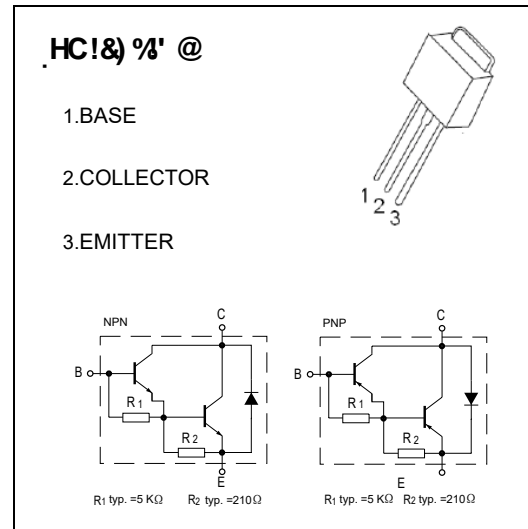


TO-251-3L Plastic-Encapsulate Transistors

A>8 %&& TRANSISTOR (NPN)

: 95HI F9G'

- High DC Current Gain
- Electrically Similar to Popular TIP122
- Built-in a Damper Diode at E-C



A5L=AI A'F5HB; G (Ta=25°C unless otherwise noted)

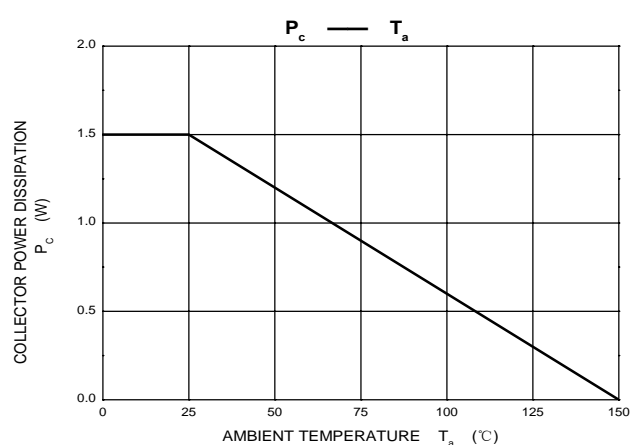
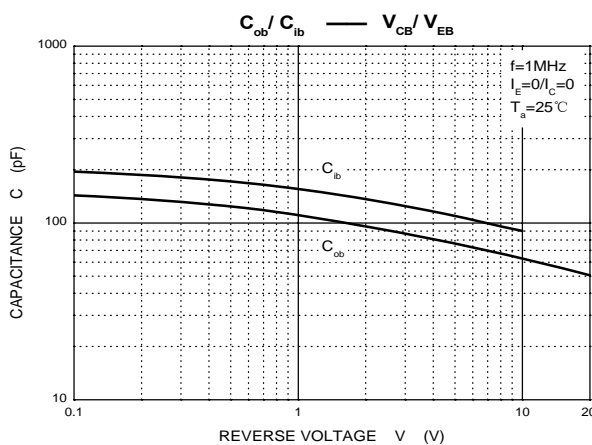
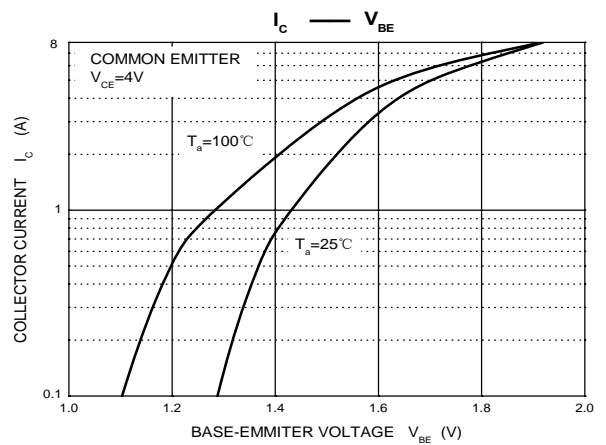
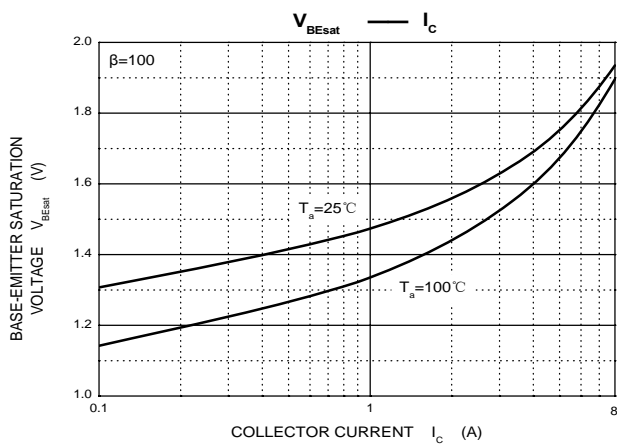
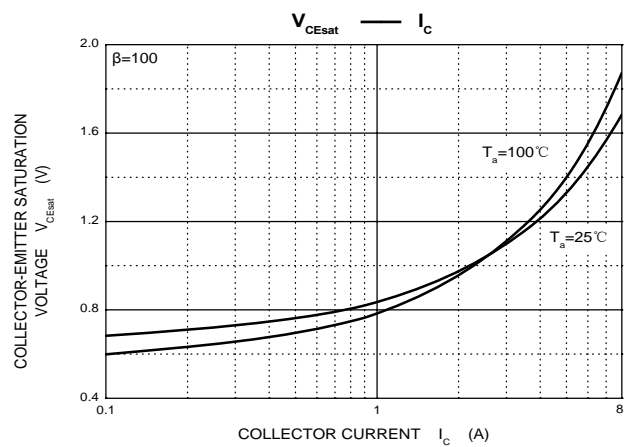
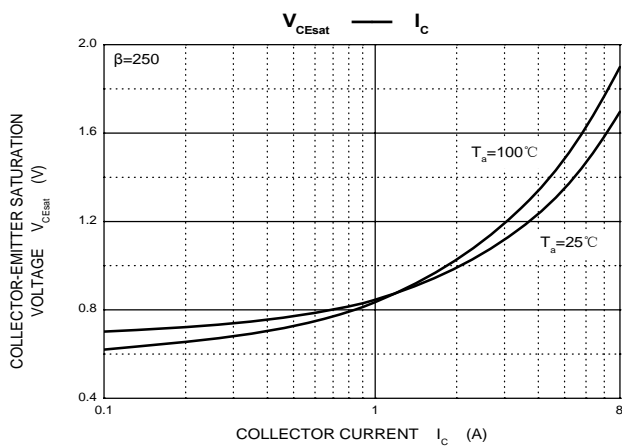
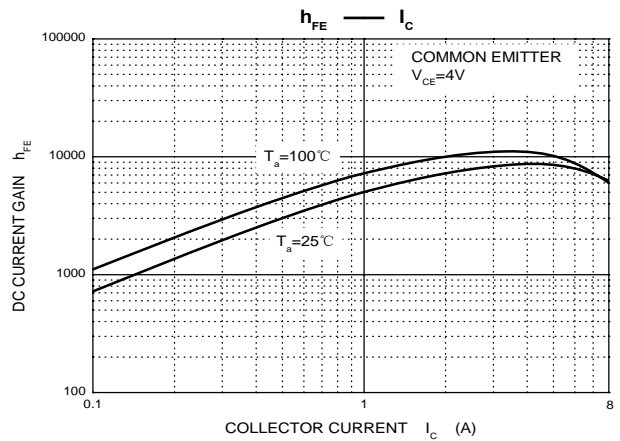
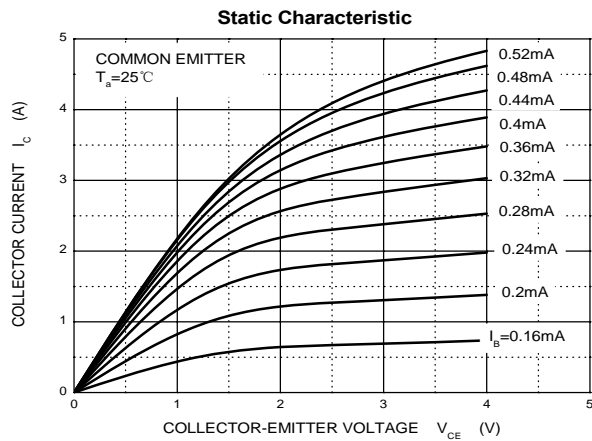
Parameter	Description	Value	Unit
V_{76C}	Collector-Base Voltage	100	V
V_{79C}	Collector-Emitter Voltage	100	V
V_{96C}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	8	A
D_T	Collector Dissipation	1.5	W
T_{stg}	Operation Junction and Storage Temperature Range	-55-150	°C

9 @ 7 HF 7 5 @ 7 < 5 F 5 7 H 9 F -GH 7 G (H1 &) °C i b' Ygg' c h Yfk jgY gd YW ZYX'

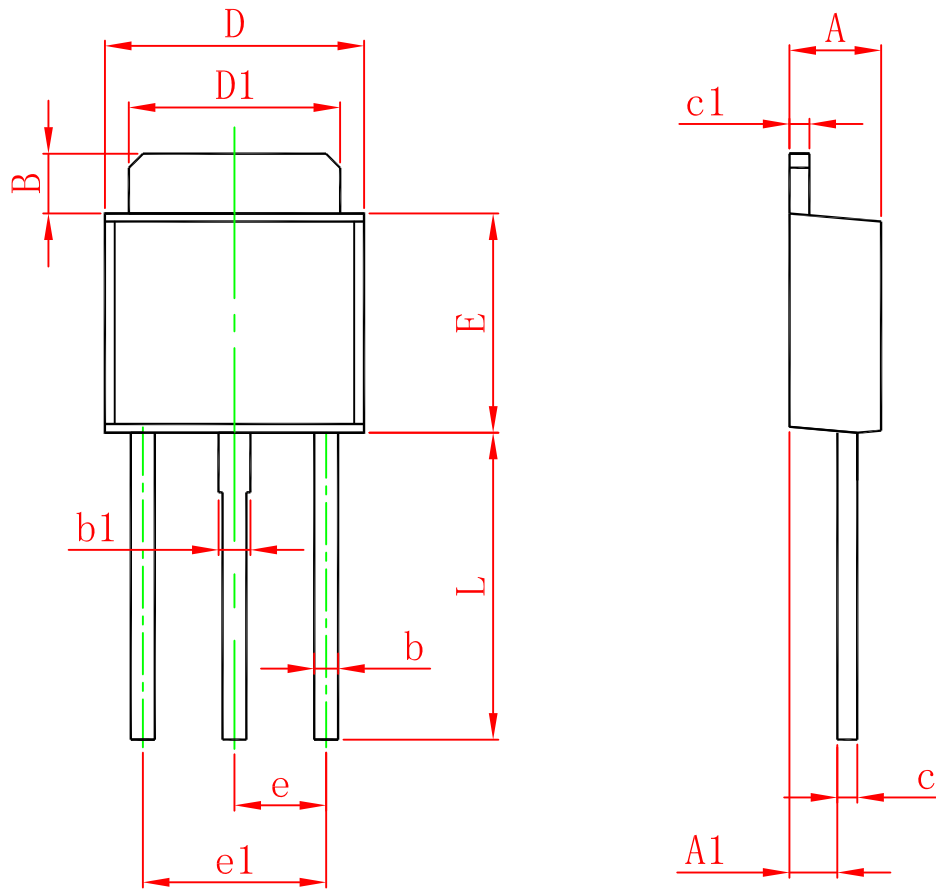
Parameter	Condition	Value	Unit
$V_{(BR)CBO}$	$I_C=1mA, I_E=0$	100	V
$V_{(BR)CEO}$	$I_C=30mA, I_B=0$	100	V
$V_{(BR)EBO}$	$I_E=3mA, I_C=0$	5	V
I_{CBO}	$V_{CB}=100V, I_E=0$	10	μA
I_{CEO}	$V_{CE}=50V, I_E=0$	10	μA
I_{EBO}	$V_{EB}=5V, I_C=0$	2	mA
$h_{FE(2)}$	$V_{CE}=4V, I_C=4A$	1000	
	$V_{CE}=4V, I_C=8A$	100	
$V_{CE(sat)1}$	$I_C=4A, I_B=16mA$	2	V
	$I_C=8A, I_B=80mA$	4	V
$V_{BE(sat)}$	$I_C=8A, I_B=80mA$	4.5	V
V_{BE}	$V_{CE}=4V, I_C=4A$	2.8	V
C_{ob}	$V_{CB}=10V, I_E=0, f=0.1MHz$	200	pF

Typical Characteristics

MJD122



TO-251-3L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	1.050	1.350	0.042	0.054
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300 TYP.		0.091 TYP.	
e1	4.500	4.700	0.177	0.185
L	7.500	7.900	0.295	0.311